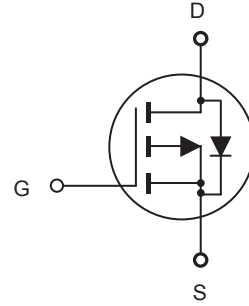


## P-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- -60V, -16A,  $R_{DS(ON)} = 86m\Omega$  @  $V_{GS} = -10V$ .  
 $R_{DS(ON)} = 125m\Omega$  @  $V_{GS} = -4.5V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Lead free product is acquired.
- TO-251 & TO-252 package.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-16	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}$	-64	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above $25^\circ\text{C}$	$P_D$	42	W
		0.33	W/ $^\circ\text{C}$
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$

[查询"CED6601"供应商](#)



# CE6601/CEU6601

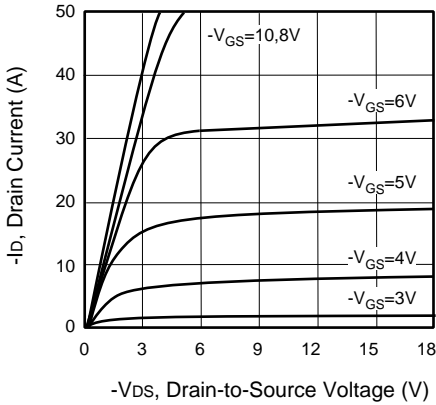


Figure 1. Output Characteristics

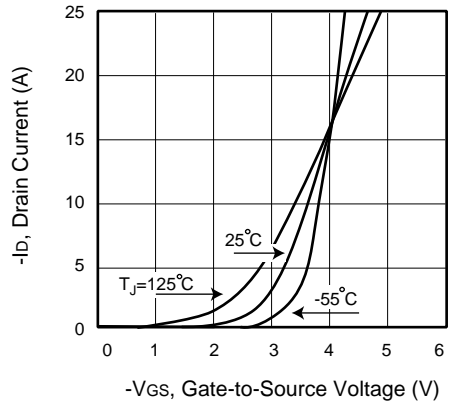


Figure 2. Transfer Characteristics

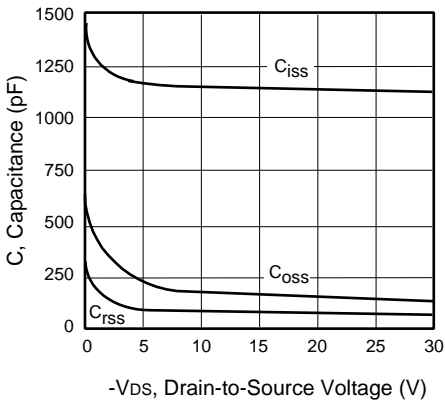


Figure 3. Capacitance

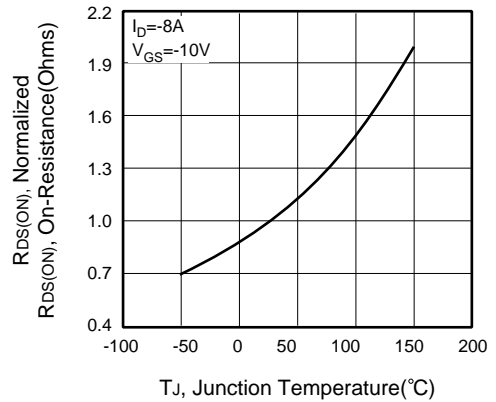


Figure 4. On-Resistance Variation with Temperature

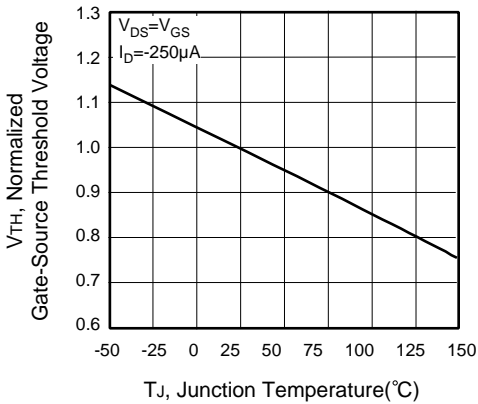


Figure 5. Gate Threshold Variation with Temperature

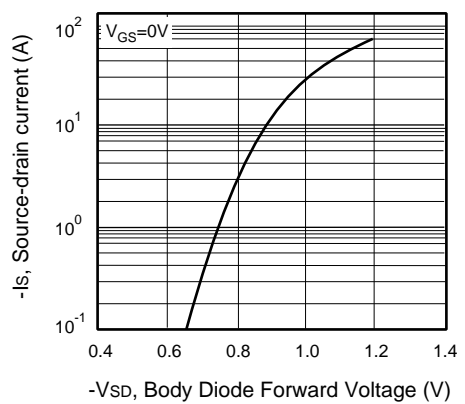
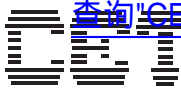


Figure 6. Body Diode Forward Voltage Variation with Source Current



# CED6601/CEU6601

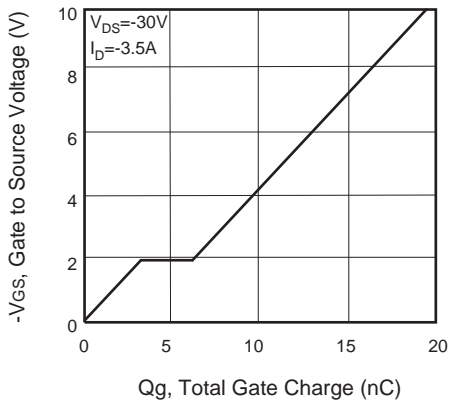


Figure 7. Gate Charge

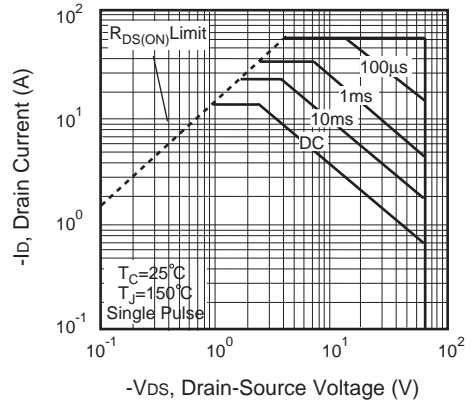


Figure 8. Maximum Safe Operating Area

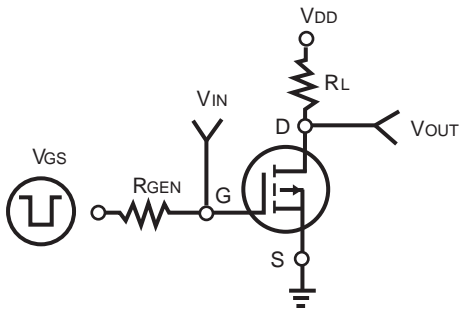


Figure 9. Switching Test Circuit

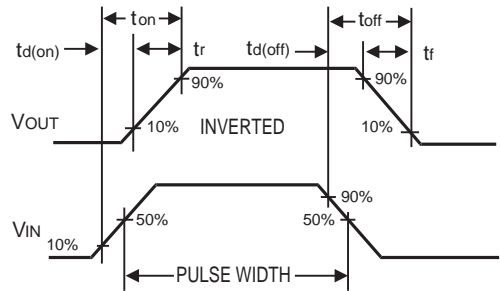


Figure 10. Switching Waveforms

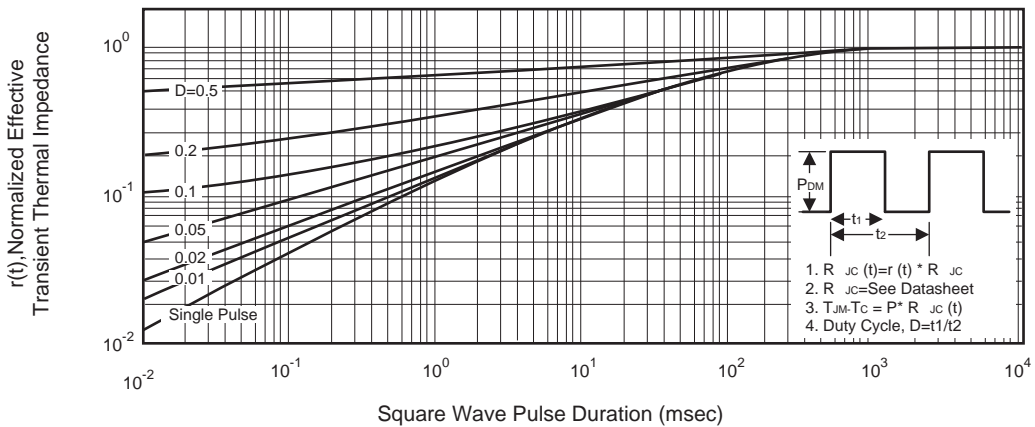


Figure 11. Normalized Thermal Transient Impedance Curve